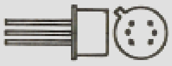
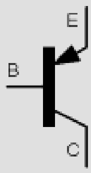
BFX11

BFX11 Silicon PNP Transistor	

Uce/Ucb:	-45/-45V	
Ic:	-0.5A	
β (Ic/Ib):	-	
N:	-	
F:	>130MHz	
Tmax:	-	

the BFX11 is a silicon PNP transistor, Uce = 45V, Ic = 500mA, applications: dual transistor, low noise

Source:	Jaeger electronic catalog 1999

Advanced Information for: BFX11	
OEM	Texas Instruments
pkg details:	TO-77

complementary:	not available for this type
similar types:	2N3726, 2N3727, 2N4015, 2N4016

see similar/compl. details
push down ↓

(CAPTURA DE INTERNET)

BFX11

CASE 654-07, STYLE 1

DUAL AMPLIFIER TRANSISTOR

PNP SILICON

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MAXIMUM RATINGS

Rating	Symbol	Value		Unit
Collector-Emitter Voltage	V_{CEO}	45		Vdc
Collector-Base Voltage	V_{CBO}	45		Vdc
Emitter-Base Voltage	V_{EBO}	4.5		Vdc
Collector Current − Continuous	I_C	100		mAdc
		One Die	Both Die	
Total Device Dissipation @ $T_A = 25°C$ Derate above 25°C	P_D	400	500	mW mW/°C
Total Device Dissipation @ $T_C = 25°C$ Derate above 25°C	P_D	0.85	1.4	Watts mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	−65 to +200		°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage(1)	(I_C = 10 mA, I_B = 0)	$V_{CEO(sus)}$		45	Vdc
Collector-Base Breakdown Voltage	(I_C = 10 μA, I_E = 0)	$V_{(BR)CBO}$		45	Vdc
Emitter-Base Breakdown Voltage	(I_C = 0, I_E = 10 μA)	$V_{(BR)EBO}$		4.5	Vdc
Collector Cutoff Current	(V_{CB} = 30 Vdc, I_E = 0) (V_{CB} = 30 Vdc, I_E = 0, T_A = 150°C)	I_{CBO}		10 10	nAdc μAdc
Emitter Cutoff Current	(I_C = 0, V_{EB} = 3 Vdc)	I_{EBO}		100	nAdc
ON CHARACTERISTICS					
DC Current Gain	(I_C = 10 μA, V_{CE} = 5 Vdc) (I_C = 100 μA, V_{CE} = 5 Vdc) (I_C = 1 mA, V_{CE} = 5 Vdc) (I_C = 50 mA, V_{CE} = 5 Vdc)	h_{FE}	50 80 90 80	— — — —	— — — —
Collector-Emitter Saturation Voltage	(I_C = 50 mAdc, I_B = 2.5 mAdc)	$V_{CE(sat)}$	—	0.25	Vdc
Base-Emitter Saturation Voltage	(I_C = 50 mAdc, I_B = 2.5 mAdc)	$V_{BE(sat)}$	—	1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain − Bandwidth Product	(I_C = 50 mAdc, V_{CE} = 20 Vdc, f = 100 MHz)	f_T	130	—	MHz
Output Capacitance	(V_{CB} = 10 Vdc, I_E = 0, f = 140 kHz)	C_{obo}	—	8	pF
Input Capacitance	(V_{EB} = 0.5 Vdc, I_C = 0, f = 140 kHz)	C_{ibo}	—	25	pF
Noise Figure	(I_C = 30 μAdc, V_{CE} = 5 Vdc, R_S = 10 kohms, f = 1 kHz)	NF	—	5	dB
MATCHING CHARACTERISTICS					
DC Current Gain Ratio(2)	(I_C = 100 μAdc, V_{CE} = 5 Vdc)	h_{FE1}/h_{FE2}	0.8	1	—
Base-Emitter Voltage Differential	(I_C = 100 μAdc, V_{CE} = 5 Vdc)	$\|V_{BE1}-V_{BE2}\|$	—	5	mVdc
Base-Emitter Voltage Differential Gradient	(I_C = 100 μAdc, V_{CE} = 5 Vdc, T_A = −55°C to +125°C)	$\frac{\Delta(V_{BE1}-V_{BE2})}{\Delta T_A}$	—	20	μV/°C

(1) Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
(2) Lowest h_{FE} reading is taken as h_{FE1} for this ratio.